

## INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

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PATENT &amp; TRADEMARK OFFICE

Docket Number (Optional)

BUR920010127US1

Application Number

Not Yet Assigned

Applicant(s)

Abadeer, et al.

Filing Date

Concurrently herewith

Group Art Unit

N t Yet Assigned

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MBS		US 6,180,464 B1	1/30/01	Krivokapic, et al.	—	—	
		US 5,379,321	1/3/95	Girmay	—	—	
		US 5,532,175	7/2/96	Racanelli	—	—	
		US 5,457,336	10/10/95	Fang, et al.	—	—	
		US 6,047,247	4/4/00	Iwanishi, et al	—	—	
		US 5,654,896	8/5/97	Ochi	—	—	
		US 5,696,452	12/9/97	Hemmenway, et al	—	—	
		US 5,900,741	5/4/99	Roohparvar	—	—	
MBS		US 5,587,665	12/24/96	Jiang	—	—	

## FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)


EXAMINER

SHINGLETON

DATE CONSIDERED

July 1, 2003

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>		Docket Number (Optional) <b>BUR9200100127651</b>	Application Number <b>Not Yet Assigned</b>
Applicant(s) <b>Abadeer et al.</b>		Filing Date <b>Concurrently Herewith</b>	Group Art Unit <b>Not Yet Assigned</b>

  

*EXAMINER INITIAL	OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>
MBS	S. Ogasawara and N. Shiono, "Generalized Diffusion-Reaction model for the Low-Field Charge-Buildup Instability at the Si-SiO <sub>2</sub> Interface, "Phys. Rev. B, vol. 51, pp. 4218-4230, 1995.
MBS	Wagdi W. Abadeer, William R. Tonti, Wilfried H. Hansch, and Udo Schwalke, "Long-Term Temperature Reliability of P+ Polysilicon Gated Devices, "IEEE TRANSACTIONS ON ELECTRON DEVICES, vol. 42, No. 2, pp. 360-362, 1995.
MBS	Shigeo Ogawa, Masakazu Shimaya, and Noburu Shiono, "Interface-Trap Generation at Ultra-thin SiO <sub>2</sub> (4-6 nm)-Si Interfaces During Negative-Bias Temperature Aging, "J. Appl. Phys. 77 (3), 1 February 1995, pp. 1137-1148, 1995.
MBS	G. LaRosa, F. Guarin, S. Rauch, A. Acovic, J. Lukaitis, and E. Crabbe, "NBTI-Channel Hot Carrier Effects in PMOSFETS in Advanced CMOS Technologies, "Proceedings of the 35th Annual IEEE International Reliability Physics Symposium (IRPS), pp. 282-286, 1997.
MBS	Toveji Yamamoto, Ken ichi Uwasawa, and Tohru Mogami, "Bias Temperature Instability in Scaled P+ Polysilicon Gate p-MOSFET's, "IEEE Transactions on Electron Devices, vol. 46, No. 5, pp. 921-926, 1999.
MBS	Mariko Makabe, Taishi Kubota, and Tomohisa Kitano, "Bias-Temperature Degradation of pMOSFETs: Mechanism and Suppression, "Proceedings of the 38th Annual IEEE International Physics Symposium (IRPS), pp. 205-209, 2000.
MBS	C.H. Liu, Y.F. Chen, S.K. Fan, M.T. Lee, M.H. Lin, C.H. Chou, W.C. Chang, S.C. Huang, Y.J. Cjang, and K.Y. Fu, "Negative Bias Temperature Instability (NBTI) in Deep Sub-Micron P+ Gate pMOSFETs, "Proceedings of the International Integrated Reliability Workshop, pp 98-100, 2000.
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